

THYRISTOR MODULE

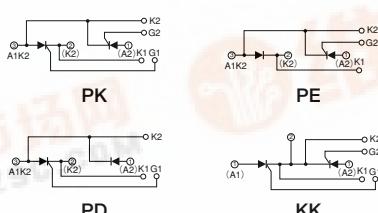
PK(PD,PE,KK)70F

Power Thyristor/Diode Module PK70F series are designed for various rectifier circuits and power controls. For your circuit application, following internal connections and wide voltage ratings up to 1,600V are available. High precision 25mm (1inch) width package and electrically isolated mounting base make your mechanical design easy.

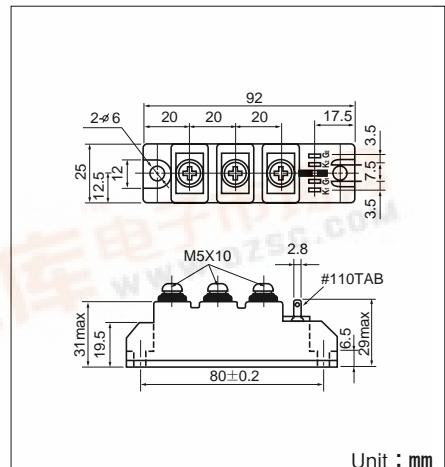
- $I_{T(AV)} = 70A$, $I_{T(RMS)} = 110A$, $I_{TSM} = 1950A$
 - $di/dt = 150 A/\mu s$
 - $dv/dt = 500V/\mu s$

(Applications)

- Various rectifiers
- AC/DC motor drives
- Heater controls
- Light dimmers
- Static switches



UL:E76102(M)



■ Maximum Ratings

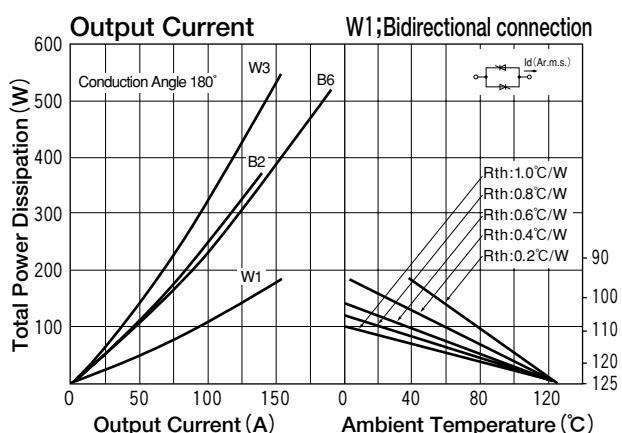
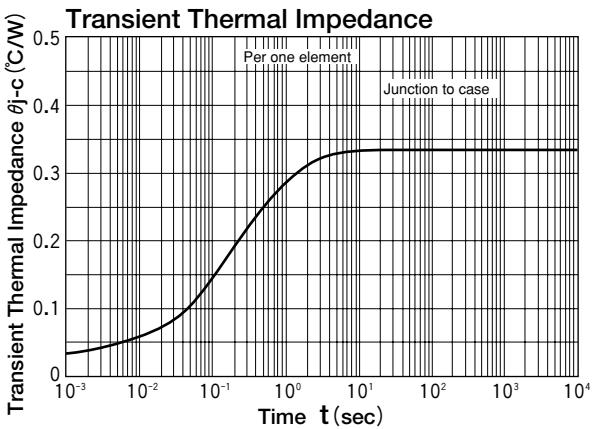
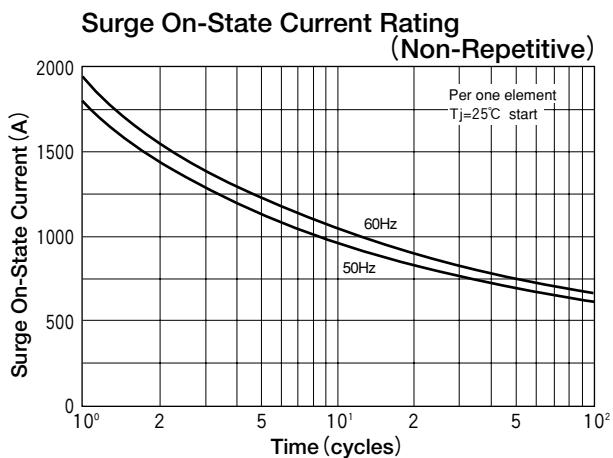
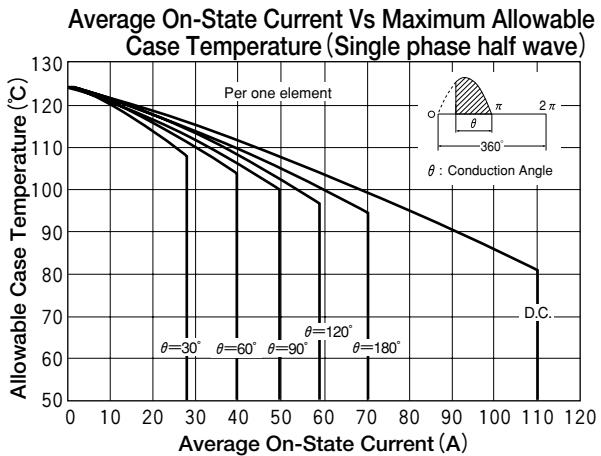
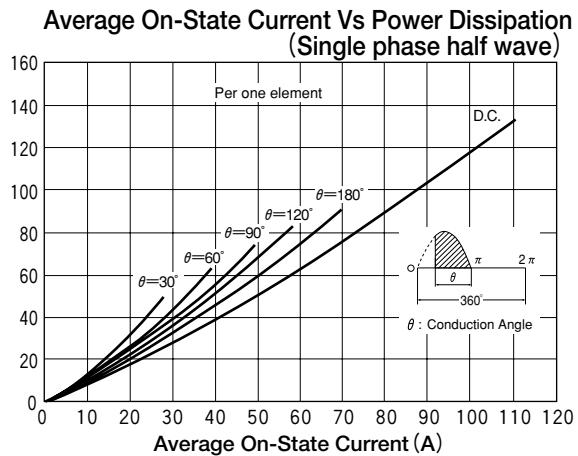
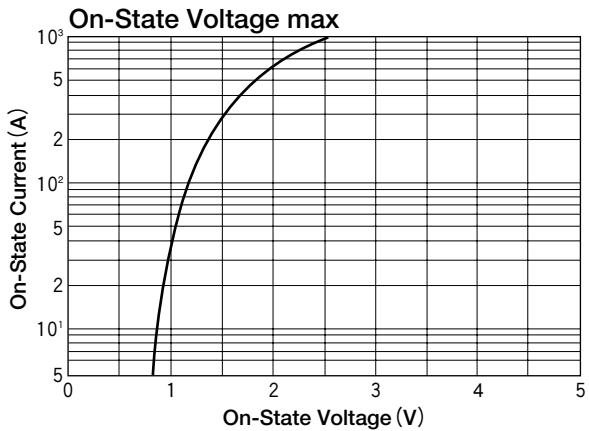
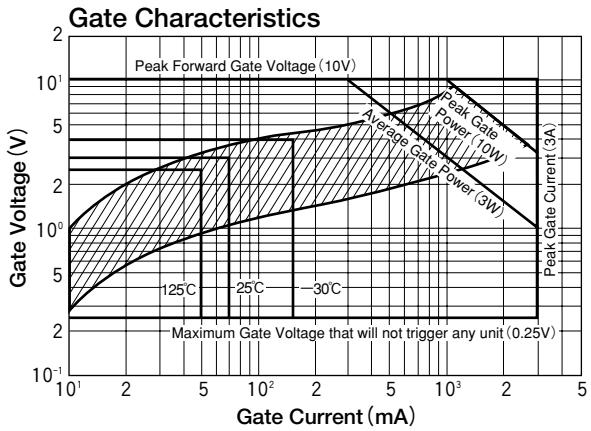
Symbol	Item	Ratings				Unit
		PK70F40	PK70F80	PK70F120	PK70F160	
V _{RRM}	* Repetitive Peak Reverse Voltage	400	800	1200	1600	V
V _{RSM}	* Non-Repetitive Peak Reverse Voltage	480	960	1300	1700	V
V _{DRM}	Repetitive Peak Off-State Voltage	400	800	1200	1600	V

Symbol	Item	Conditions	Ratings	Unit
I _{T(AV)}	* Average On-State Current	Single phase, half wave, 180° conduction, T _c : 94°C	70	A
I _{T(RMS)}	* R.M.S. On-State Current	Single phase, half wave, 180° conduction, T _c : 94°C	110	A
I _{TSM}	* Surge On-State Current	½cycle, 50Hz/60Hz, peak Value, non-repetitive	1800/1950	A
I ² t	* I ² t	Value for one cycle of surge current	16200	A ² S
P _{GM}	Peak Gate Power Dissipation		10	W
P _{G(AV)}	Average Gate Power Dissipation		3	W
I _{FGM}	Peak Gate Current		3	A
V _{FGM}	Peak Gate Voltage (Forward)		10	V
V _{RGM}	Peak Gate Voltage (Reverse)		5	V
di/dt	Critical Rate of Rise of On-State Current	I _G =100mA, T _j =25°C, V _D =½V _{DRM} , dI _G /dt=0.1A/μs	150	A/μs
V _{iso}	* Isolation Breakdown Voltage (R.M.S.)	A.C.1minute	2500	V
T _j	* Operating Junction Temperature		-40 to +125	°C
T _{tsg}	* Storage Temperature		-40 to +125	°C
Mounting Torque	Mounting (M5)	Recommended Value 1.5-2.5 (15-25)	2.7 (28)	N·m (kgf·cm)
	Terminal (M5)	Recommended Value 1.5-2.5 (15-25)	2.7 (28)	
	Mass		170	g

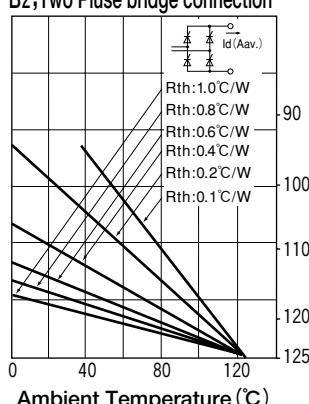
■ Electrical Characteristics

Symbol	Item	Conditions	Ratings	Unit
I _{DRM}	Repetitive Peak Off-State Current, max.	at V _{DRM} , single phase, half wave, T _j =125°C	15	mA
I _{RRM}	* Repetitive Peak Reverse Current, max.	at V _{DRM} , single phase, half wave, T _j =125°C	15	mA
V _{TM}	* Peak On-State Voltage, max.	On-State Current 220A, T _j =25°C Inst. measurement	1.40	V
I _{GT} /V _{GT}	Gate Trigger Current/Voltage, max.	T _j =25°C, I _G =1A, V _D =6V	70/3	mA/V
V _{GD}	Non-Trigger Gate, Voltage. min.	T _j =125°C, V _D =½V _{DRM}	0.25	V
t _{gt}	Turn On Time, max.	I _G =70A, I _G =100mA, T _j =25°C, V _D =½V _{DRM} , dI _G /dt=0.1A/μs	10	μs
dV/dt	Critical Rate of Rise of Off-State Voltage, min.	T _j =125°C, V _D =⅔V _{DRM} , Exponential wave.	500	V/μs
I _H	Holding Current, typ.	T _j =25°C	50	mA
I _{latch}	Latching Current, typ.	T _j =25°C	100	mA
R _{th(j-c)}	* Thermal Impedance, max.	Junction to case	0.33	°C/W

PK(PD,PE,KK)70F



B2; Two Pulse bridge connection



B6; Six pulse bridge connection

W3; Three phase bidirectional connection

Allowable Case Temperature (°C)

